

12-11-06

**IN THE CLAIMS**

Please amend the claims as follows.

1. (Currently Amended) A process comprising:
  - forming a first recess in a substrate;
  - forming a conductive structure in the first recess having vertical sidewalls;
  - first wet etching to expose a first portion of the conductive structure;
  - first rinsing the conductive structure; and
  - second non-wet etching to expose a second portion of the conductive structure, wherein the exposed first and second portions of the conductive structure extend vertically above the substrate.
2. (Original) The process of claim 1, wherein first wet etching includes first etching a polysilicon sacrificial second film that is disposed over the substrate.
3. (Original) The process of claim 1, and wherein first wet etching is at a rate that is faster than second non-wet etching.
4. (Currently Amended) A process comprising:
  - forming a first recess in a substrate;
  - forming a conductive structure in the first recess;
  - first etching to expose a first portion of the conductive structure;
  - first rinsing the conductive structure; and
  - second etching to expose a second portion of the conductive structure

wherein first etching is selected from the group consisting of a wet process and a vapor process, and wherein second etching is selected from the group consisting of a vapor process and a dry process, wherein the exposed first and second portions of the conductive structure extend vertically above the substrate.

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